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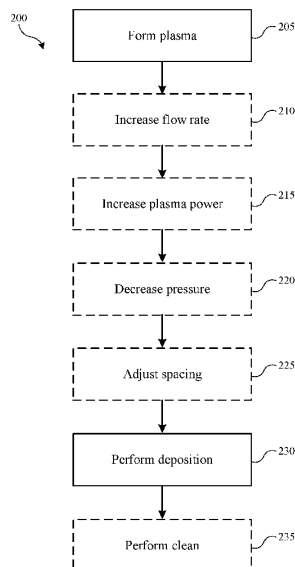


FIG. 2

(57) Abstract: Exemplary methods of semiconductor processing may include forming a plasma of a carbon-containing precursor and an inert precursor within a processing region of a semiconductor processing chamber. The methods may include, subsequent a first period of time, increasing a flow rate of the carbon-containing precursor and a flow rate of the inert precursor. The methods may include increasing a plasma power at which the plasma is formed. The methods may include performing a deposition process on a semiconductor substrate disposed within the processing region of the semiconductor processing chamber.

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